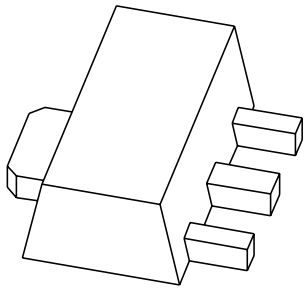


DATA SHEET



PBSS5350X

50 V, 3 A

PNP low V_{CEsat} (BISS) transistor

Product data sheet
Supersedes data of 2003 Nov 21

2004 Nov 04

50 V, 3 A PNP low V_{CEsat} (BISS) transistor

PBSS5350X

FEATURES

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements.

APPLICATIONS

- Power management
 - DC/DC converters
 - Supply line switching
 - Battery charger
 - LCD backlighting.
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs).
 - Inductive load driver (e.g. relays, buzzers and motors).

DESCRIPTION

PNP low V_{CEsat} transistor in a SOT89 plastic package.
NPN complement: PBSS4350X.

MARKING

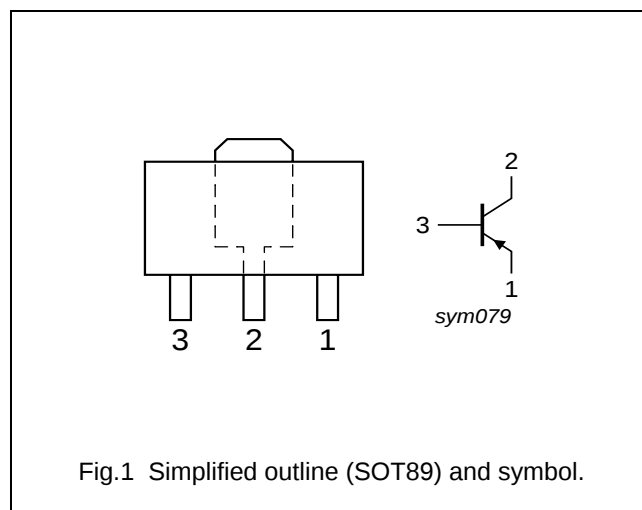
TYPE NUMBER	MARKING CODE
PBSS5350X	S46

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–50	V
I_C	collector current (DC)	–3	A
I_{CM}	peak collector current	–5	A
R_{CEsat}	equivalent on-resistance	135	m Ω

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



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ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS5350X	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

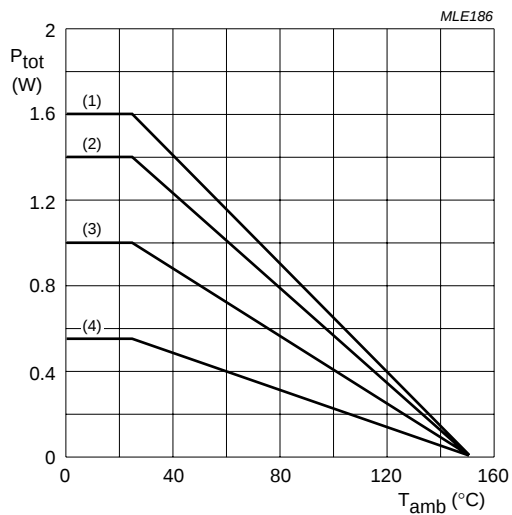
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–50	V
V_{CEO}	collector-emitter voltage	open base	–	–50	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)	note 4	–	–3	A
I_{CM}	peak collector current	limited by $T_{j(max)}$	–	–5	A
I_B	base current (DC)		–	–0.5	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$ note 1 note 2 note 3 note 4	– – – –	550 1 1.4 1.6	mW W W W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

Notes

1. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; standard footprint.
2. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; mounting pad for collector 1 cm².
3. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; mounting pad for collector 6 cm².
4. Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.

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- | | |
|--|--|
| (1) Ceramic PCB; 7 cm ²
mounting pad for collector. | (3) FR4 PCB; 1 cm ² copper
mounting pad for collector. |
| (2) FR4 PCB; 6 cm ² copper
mounting pad for collector. | (4) Standard footprint. |

Fig.2 Power derating curves.

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PNP low V_{CEsat} (BISS) transistor

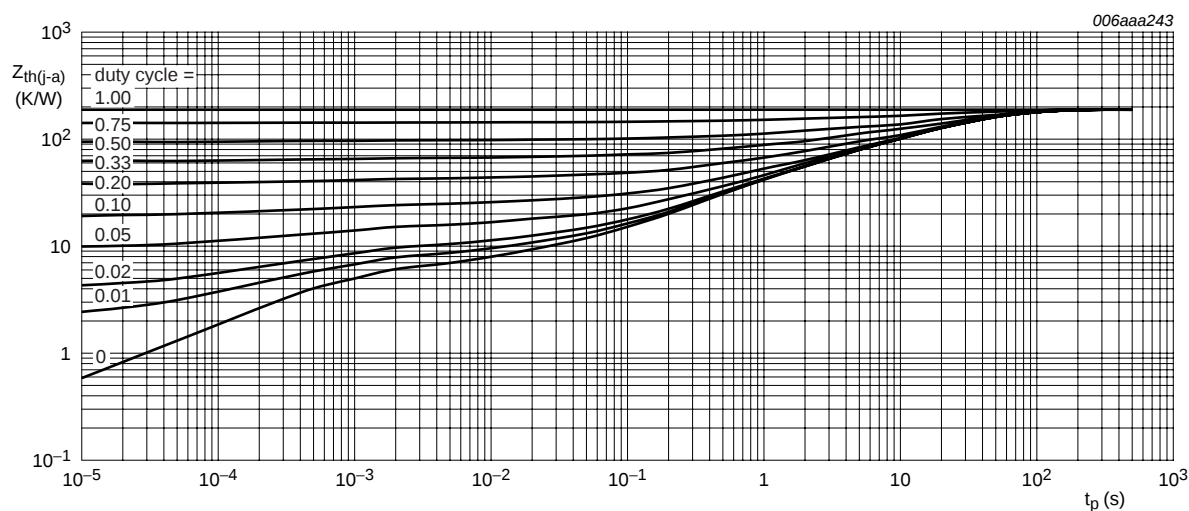
PBSS5350X

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		
		note 1	225	K/W
		note 2	125	K/W
		note 3	90	K/W
		note 4	80	K/W
$R_{th(j-s)}$	thermal resistance from junction to soldering point		16	K/W

Notes

1. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; standard footprint.
2. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; mounting pad for collector 1 cm².
3. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; mounting pad for collector 6 cm².
4. Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.

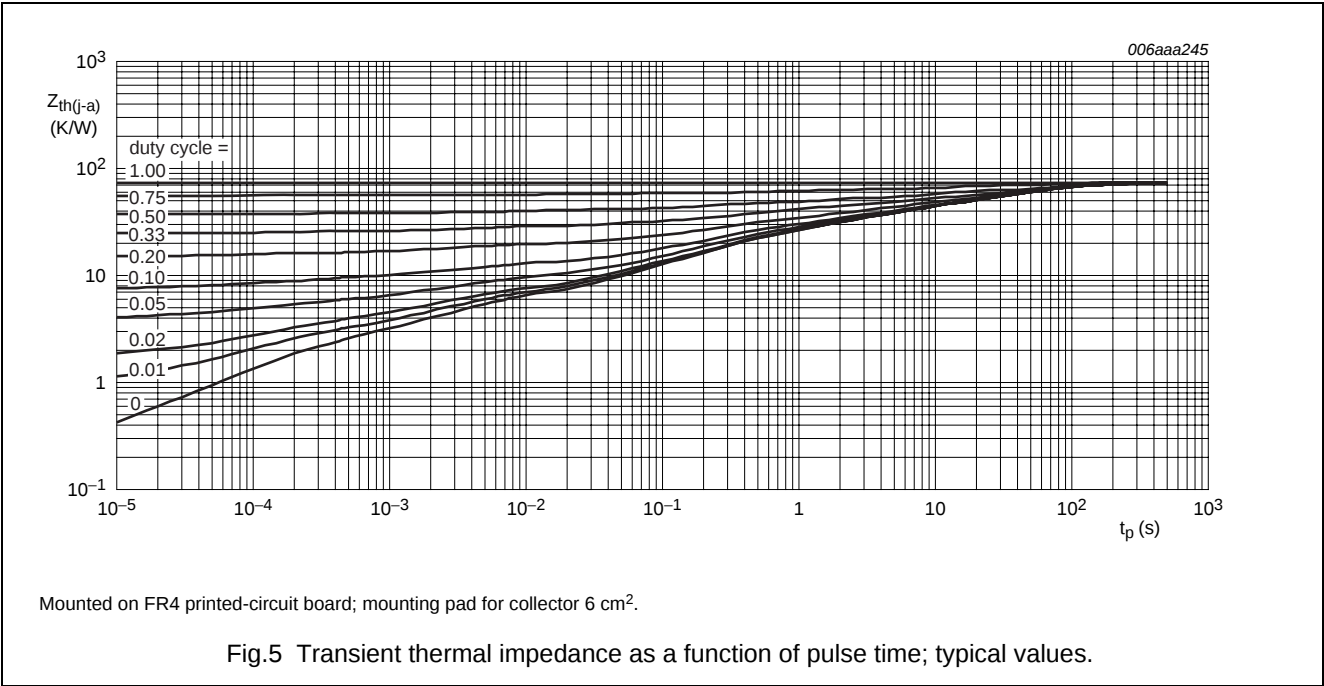
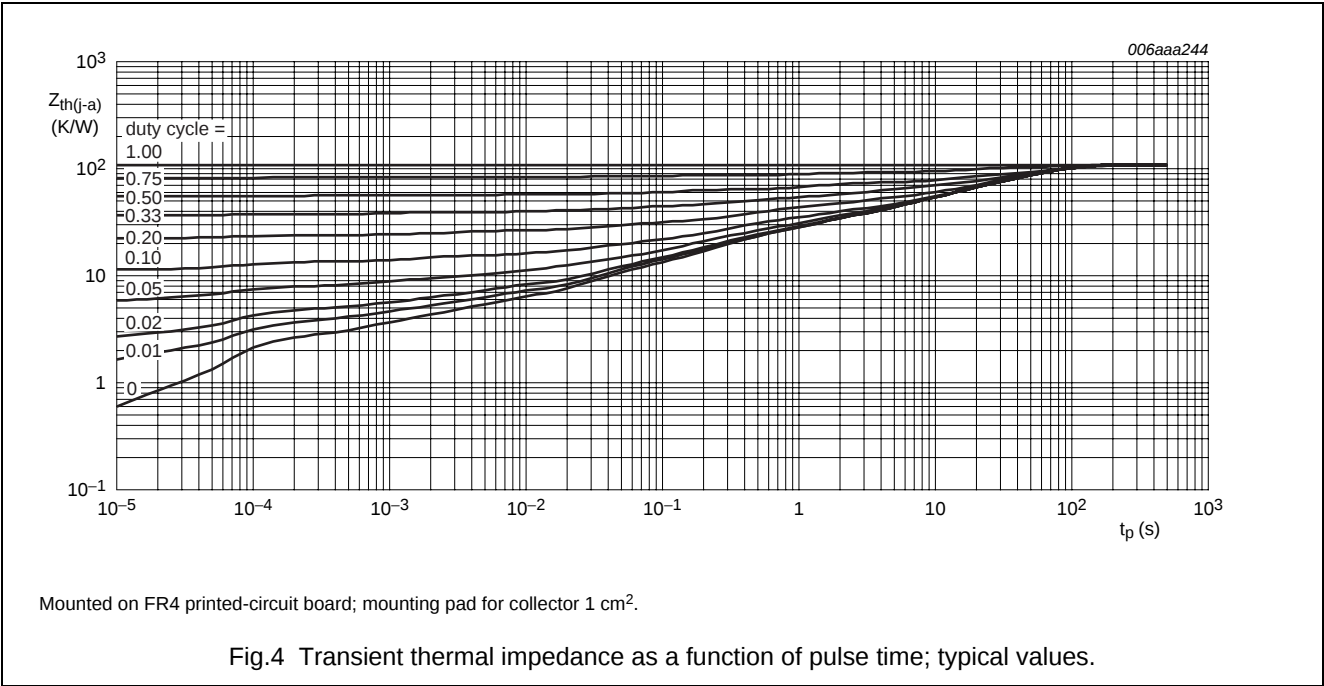


Mounted on FR4 printed-circuit board; standard footprint.

Fig.3 Transient thermal impedance as a function of pulse time; typical values.

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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

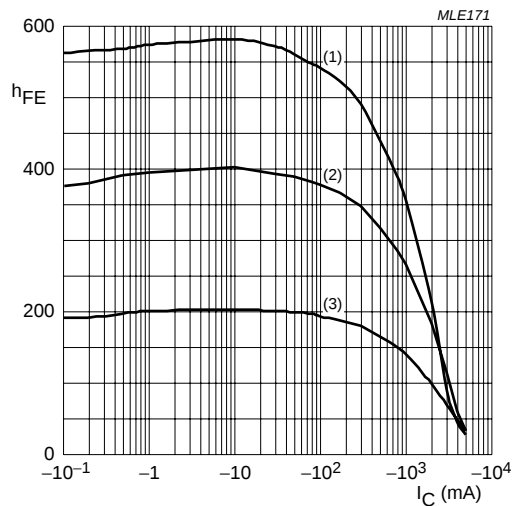
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -50\text{ V}; I_E = 0\text{ A}$	–	–	–100	nA
		$V_{CB} = -50\text{ V}; I_E = 0\text{ A}; T_J = 150\text{ }^{\circ}\text{C}$	–	–	–50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = -50\text{ V}; V_{BE} = 0\text{ V}$	–	–	–100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	–	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -2\text{ V}$ $I_C = -0.1\text{ A}$	200	–	–	
		$I_C = -0.5\text{ A}$	200	–	–	
		$I_C = -1\text{ A}; \text{note 1}$	200	–	450	
		$I_C = -2\text{ A}; \text{note 1}$	130	–	–	
		$I_C = -3\text{ A}; \text{note 1}$	80	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -0.5\text{ A}; I_B = -50\text{ mA}$	–	–	–90	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	–180	mV
		$I_C = -2\text{ A}; I_B = -100\text{ mA}$	–	–	–320	mV
		$I_C = -2\text{ A}; I_B = -200\text{ mA}; \text{note 1}$	–	–	–270	mV
		$I_C = -3\text{ A}; I_B = -300\text{ mA}; \text{note 1}$	–	–	–390	mV
R_{CEsat}	equivalent on-resistance	$I_C = -2\text{ A}; I_B = -200\text{ mA}; \text{note 1}$	–	90	135	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = -2\text{ A}; I_B = -100\text{ mA}$	–	–	–1.1	V
		$I_C = -3\text{ A}; I_B = -300\text{ mA}; \text{note 1}$	–	–	–1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -1\text{ A}$	–1.1	–	–	V
f_T	transition frequency	$I_C = -100\text{ mA}; V_{CE} = -5\text{ V};$ $f = 100\text{ MHz}$	100	–	–	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$	–	–	35	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

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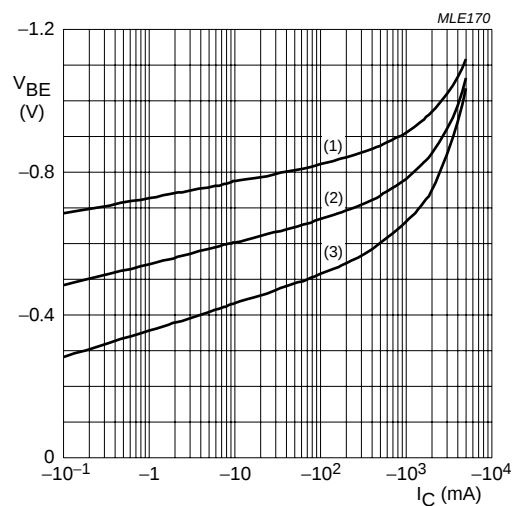
PBSS5350X



$V_{CE} = -2$ V.

- (1) $T_{amb} = 100$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

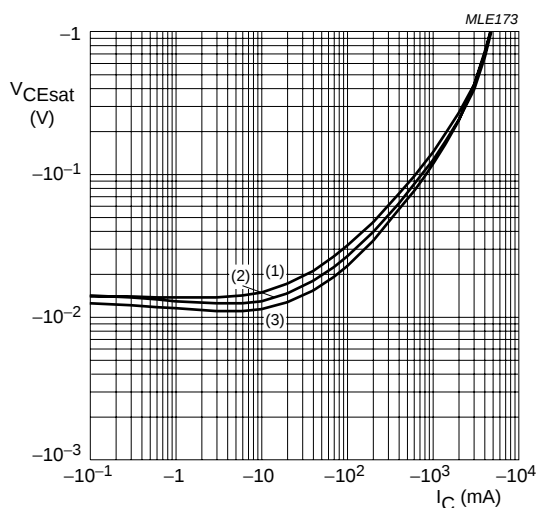
Fig.6 DC current gain as a function of collector current; typical values.



$V_{CE} = -2$ V.

- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 100$ °C.

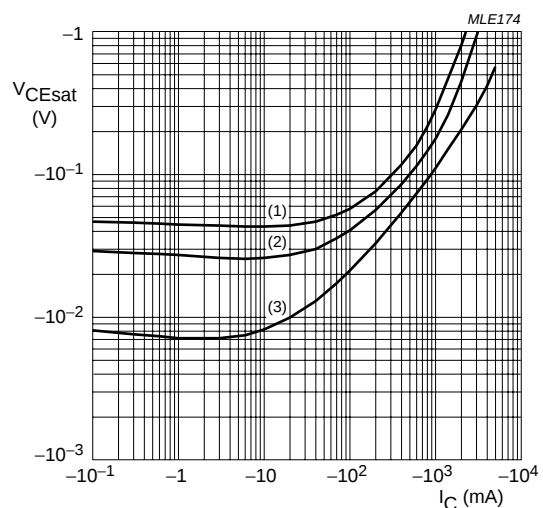
Fig.7 Base-emitter voltage as a function of collector current; typical values.



$I_C/I_B = 20$.

- (1) $T_{amb} = 100$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



$T_{amb} = 25$ °C.

- (1) $I_C/I_B = 100$.
- (2) $I_C/I_B = 50$.
- (3) $I_C/I_B = 10$.

Fig.9 Collector-emitter saturation voltage as a function of collector current; typical values.

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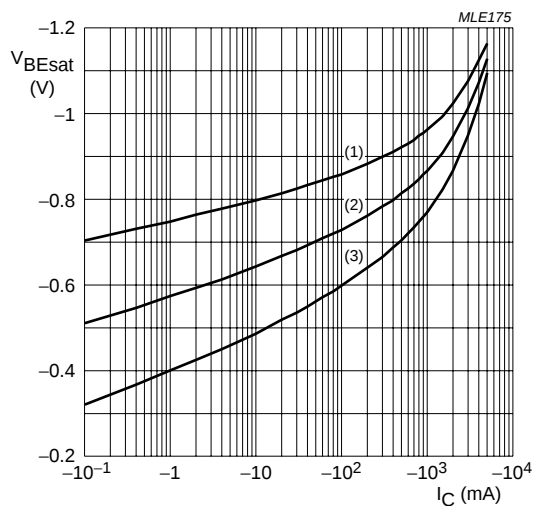
 $I_C/I_B = 20$.(1) $T_{amb} = -55^\circ\text{C}$. (2) $T_{amb} = 25^\circ\text{C}$. (3) $T_{amb} = 100^\circ\text{C}$.

Fig.10 Base-emitter saturation voltage as a function of collector current; typical values.

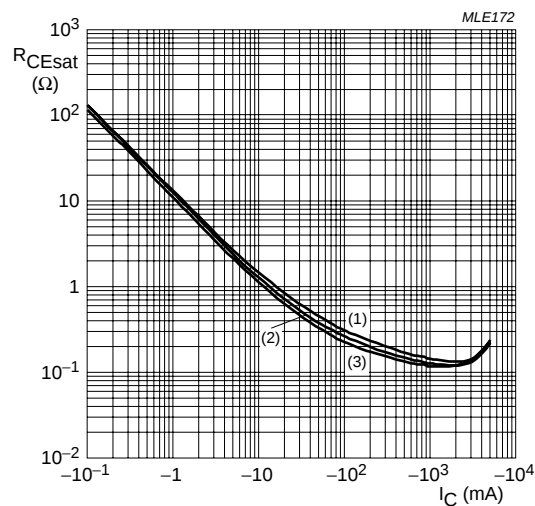
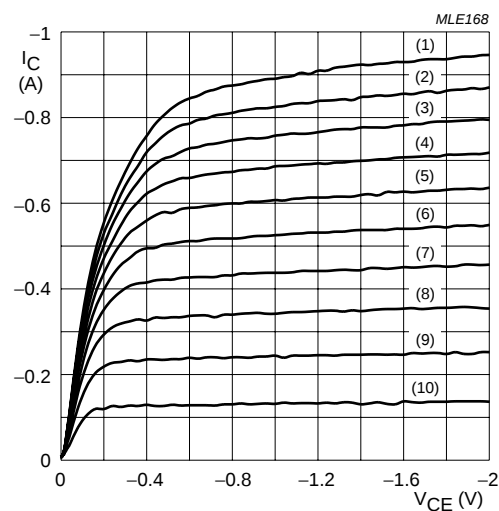
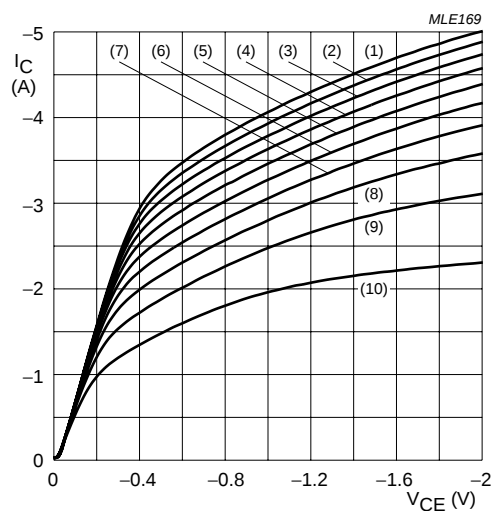
 $I_C/I_B = 20$.(1) $T_{amb} = 150^\circ\text{C}$. (2) $T_{amb} = 25^\circ\text{C}$. (3) $T_{amb} = -55^\circ\text{C}$.

Fig.11 Equivalent on-resistance as a function of collector current; typical values.

 $T_{amb} = 25^\circ\text{C}$.

(1) $I_B = -3500 \mu\text{A}$.	(5) $I_B = -2100 \mu\text{A}$.	(9) $I_B = -700 \mu\text{A}$.
(2) $I_B = -3150 \mu\text{A}$.	(6) $I_B = -1750 \mu\text{A}$.	(10) $I_B = -350 \mu\text{A}$.
(3) $I_B = -2800 \mu\text{A}$.	(7) $I_B = -1400 \mu\text{A}$.	
(4) $I_B = -2450 \mu\text{A}$.	(8) $I_B = -1050 \mu\text{A}$.	

Fig.12 Collector current as a function of collector-emitter voltage; typical values.

 $T_{amb} = 25^\circ\text{C}$.

(1) $I_B = -140 \text{ mA}$.	(5) $I_B = -84 \text{ mA}$.	(9) $I_B = -28 \text{ mA}$.
(2) $I_B = -126 \text{ mA}$.	(6) $I_B = -70 \text{ mA}$.	(10) $I_B = -14 \text{ mA}$.
(3) $I_B = -112 \text{ mA}$.	(7) $I_B = -56 \text{ mA}$.	
(4) $I_B = -98 \text{ mA}$.	(8) $I_B = -42 \text{ mA}$.	

Fig.13 Collector current as a function of collector-emitter voltage; typical values.

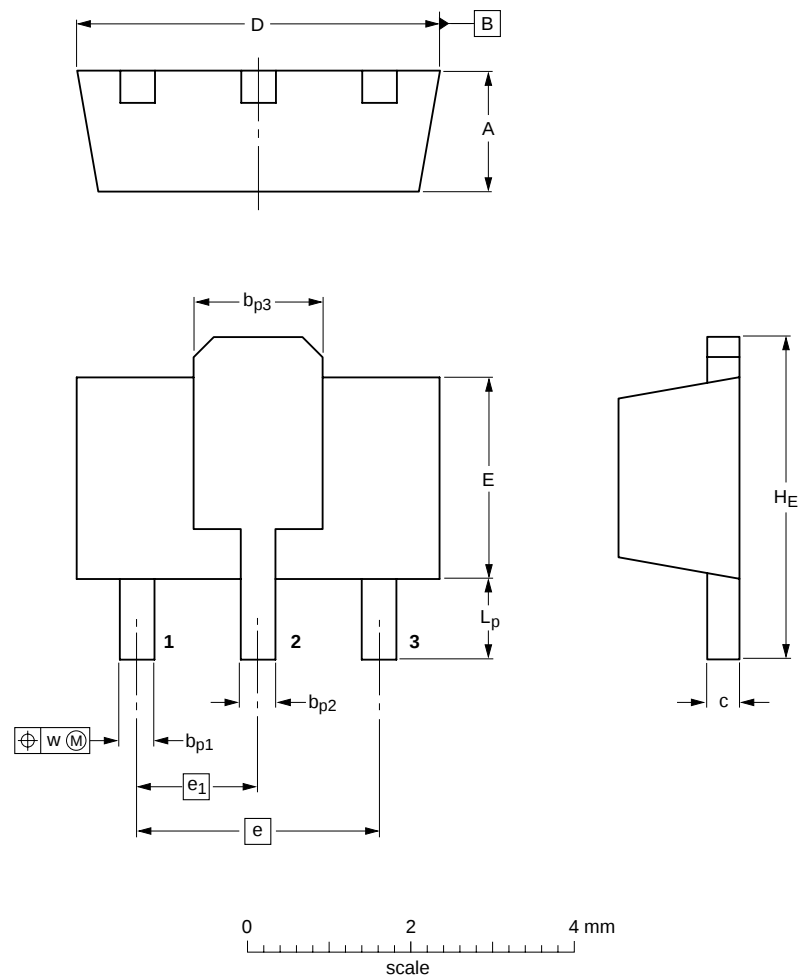
50 V, 3 A
PNP low V_{CEsat} (BISS) transistor

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PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _{p1}	b _{p2}	b _{p3}	c	D	E	e	e ₁	H _E	L _p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT89		TO-243	SC-62			04-08-03 06-03-16

50 V, 3 A PNP low V_{CEsat} (BISS) transistor

PBSS5350X

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Contact information

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